

Amendments to the claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of claims:

Claim 1 (currently amended): A crystal growth apparatus for a semiconductor thin film for radiating laser light to a semiconductor thin film formed on a base material to cause crystal growth of said semiconductor thin film in a direction substantially parallel to a main surface of said base material, comprising:

first radiation means for selectively radiating first laser light having a wavelength in the ultraviolet region to said semiconductor thin film to melt a crystallization target area of said semiconductor thin film, wherein the first laser light is ~~solid state laser light selected from the group comprising excimer laser light and or~~ YAG laser light; and

second radiation means for selectively radiating second laser light to said base material to heat said base material without melting said base material at a position corresponding to an area including said crystallization target area of said semiconductor thin film, wherein the second laser light is carbon dioxide gas laser light;

wherein said first laser light and said second laser light have different wavelengths;

wherein said first radiation means includes a mask having a plurality of slits for transmitting the first laser light, and image forming means for forming on the semiconductor thin film an image of the first laser light transmitted through the slits as an image of the mask; and

wherein said second radiation means includes a light source for producing said second laser light and irradiance distribution uniformizing means configured by a combination of a cylindrical lens array and a condenser lens for adjusting said second laser light such that said second laser light being transmitted attains uniform irradiance distribution on a plane perpendicular to its optical axis.

Claim 2 (previously presented): The crystal growth apparatus for a semiconductor thin film according to claim 1, wherein

said second radiation means further includes an aperture stop plate arranged between said irradiance distribution uniformizing means and said base material for being radiated with said second laser light to form a desired aperture image, and an objective lens arranged between said aperture stop plate and said base material for forming said aperture image on the main surface of said base material.

Claim 3 (previously presented): The crystal growth apparatus for a semiconductor thin film according to claim 2, wherein

said second radiation means is configured such that said second laser light is obliquely incident on the main surface of said base material,

said objective lens is arranged substantially perpendicular to an optical axis of said obliquely incident second laser light, and

said aperture stop plate is arranged obliquely to the optical axis of said obliquely incident second laser light such that an image plane of said aperture image substantially overlays the main surface of said base material.

Claim 4 (original): The crystal growth apparatus for a semiconductor thin film according to claim 3, wherein

an aperture provided to said aperture stop plate is adjusted to be in a trapezoidal shape such that said aperture image formed on the main surface of said base material becomes a quadrangular shape.

Claim 5 (canceled)

Claim 6 (previously presented): The crystal growth apparatus for a semiconductor thin film according to claim 2, wherein

said second radiation means is configured such that said second laser light is obliquely incident on the main surface of said base material, and

said objective lens and said aperture stop plate are arranged substantially parallel to the main surface of said base material.

Claim 7 (canceled)

Claim 8 (previously presented): The crystal growth apparatus for a semiconductor thin film according to claim 6, wherein

said second radiation means further includes radiation direction changing means arranged substantially parallel to said aperture stop plate for changing radiation direction of said second laser light such that said second laser light output from said irradiance distribution uniformizing means is obliquely incident on said aperture stop plate.

Claim 9 (original): The crystal growth apparatus for a semiconductor thin film according to claim 8, wherein said radiation direction changing means is a prism.

Claim 10 (original): The crystal growth apparatus for a semiconductor thin film according to claim 8, wherein said radiation direction changing means is a lens.

Claims 11-12 (canceled)